HTRB / HTGS TEST SYSTEMS for standard MOS or IGBT devices

Our test systems fulfil the 4 fundamental requirements on HTRB/HTGS systems for power MOS or IGBT devices

1. Exact case temperature of DUT independent on reverse power losses of tested devices
2. Reliable device sockets designed for 200°C
3. Continous measurement of DUTs to find DUTs with rising leakage current before destruction
4. Separate power supply foe each test board to run different devices in the same chamber

Test chambers :

Number of chambers : 4

Temperature range : 50°C to 200°C

Uniformity ratio of temperature in range of test boards : 150°C ± 1.2K
175°C ± 1.6K
200°C ± 2.5K

Maximum power dissipaton per test chamber : 150°C --- 145W
175°C --- 170W
200°C --- 200W

Test boards :

Possible size of test boards : 198 x 430mm
250 x 400mm

Number of boards in chamber : 4

Power supply :

Number of power supplies per test board : 2

Possible voltage range for HTRB : 0V to ± 300V
0V to ± 500V
0V to ± 1200V

Voltage range for HTGS : 0V to ± 60V

Operating system : MS Windows XP

Handling : Comfortable graphic platform

Alarm : Programmable, light or sound

System control : Continous for voltages and oven temperature with alarm and disconnection of defects parts

DUT control : Continous for bias voltage, leakage current and socket contacts with alarm and disconnections of test board by values over programmable limits

Ing. Buero s.r.o., Lozická 129, 190 16 Újezd nad Lesy - Praha 9, Czech republic
tel./fax : +420 281 971 605
web : www.ingbuero.cz e-mail : ingbuero@ingbuero.cz